PTO/SB/08B (10-01)

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Complete if Known Substitute for form 1449B/PTO 10/707,474 **Application Number INFORMATION DISCLOSURE** Filing Date 12/17/2003 STATEMENT BY APPLICANT First Named Inventor Ching-Hsiang Hsu **Group Art Unit** 2818 (use as many sheets as necessary) TRONG **Examiner Name** Sheet of Attorney Docket Number EMEP0056USA

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	1	number(s) oublisher city and/or country where oublished C.CH. HSU, et al.; A High Speed, Low Power P-Channel Flash EEPROM Using Silicon Rich Oxide as Tunneling Dielectric; Extended Abstracts of the 1992 International Conference on Solid State Device and Materials, Tsukuba, 1992, pp. 140-142			

Examiner Signature	Trong Phan	Date Consider	5/4/04
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^{*}EXAMINER: Initial If reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.

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